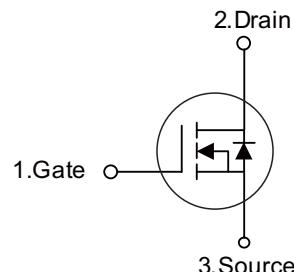


■ PRODUCT CHARACTERISTICS

VDSS	500
R _{DS(on)Typ} (@V _{GS} =10 V)	0.39Ω
Qg@type	43nC
ID	13A

Symbol



■ APPLICATIONS

- High efficiency switch mode power supplies
- Electronic ballasts
- LED power supply

■ FEATURES

- * High Switching Speed
- * 100% Avalanche Tested



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	SPF13N50	TO-220F	50 pieces/Tube
N/A	SPT13N50	TO-220	50 pieces/Tube

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V _{DSS}	500	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Continuous Drain Current	I _D	13	A	
Pulsed Drain Current (Note 2)	I _{DM}	52	A	
Avalanche Current (Note 2)	I _{AR}	13	A	
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	860	mJ	
Repetitive Avalanche Energy (Note 2)	E _{AR}	19.5	mJ	
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns	
Power Dissipation (T _C =25°C)	TO-220	P _D	195	
			W	
TO-220F			48	
			W	
Junction Temperature	T _J	+150	°C	
Storage Temperature	T _{STG}	-55~+150	°C	

Notes:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature
3. L = 6.0, I_{AS} = 13A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 13.A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	500			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}} = 500\text{V}, V_{\text{GS}} = 0\text{V}$		1		μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}} = 30\text{V}, V_{\text{DS}} = 0\text{V}$		100		nA
		$V_{\text{GS}} = -30\text{V}, V_{\text{DS}} = 0\text{V}$		-100		nA
Breakdown Voltage Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	$I_{\text{D}} = 250\mu\text{A}$ Referenced to 25°C		0.5		$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 6.5\text{A}$		0.39	0.45	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$		1580	2055	pF
Output Capacitance	C_{OSS}			180	235	pF
Reverse Transfer Capacitance	C_{RSS}			20	25	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{\text{D(ON)}}$	$V_{\text{DD}}=250\text{V}, I_{\text{D}}=13\text{A}$ $R_{\text{G}}=25\Omega$ (Note 1,2)		25	60	nS
Turn-On Rise Time	t_{R}			100	210	nS
Turn-Off Delay Time	$t_{\text{D(OFF)}}$			130	270	nS
Turn-Off Fall Time	t_{F}			100	210	nS
Total Gate Charge	Q_{G}	$V_{\text{DS}}=400\text{V}, I_{\text{D}}=13\text{A}, V_{\text{GS}}=10\text{V}$ (Note 1, 2)		43	56	nC
Gate-Source Charge	Q_{GS}			7.5		nC
Gate-Drain Charge	Q_{GD}			18.5		nC
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = 13\text{A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_{S}				13	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				52	A
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = 13\text{A},$ $dI_{\text{F}} / dt = 100\text{A}/\mu\text{s}$ (Note 1)		410		nS
Reverse Recovery Charge	Q_{RR}			4.5		μC

Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating ambient temperature

■ TEST CIRCUITS AND WAVEFORMS

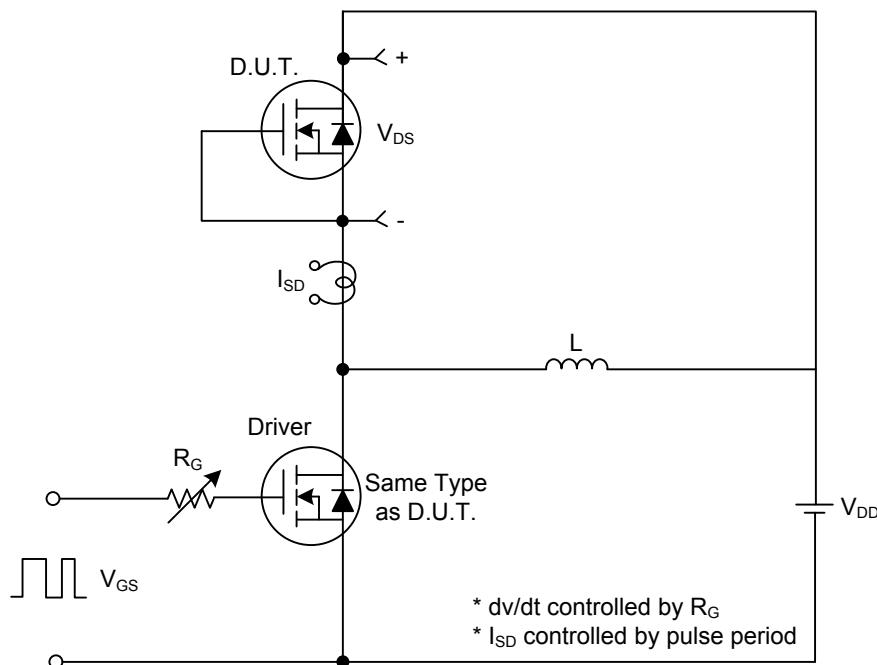


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

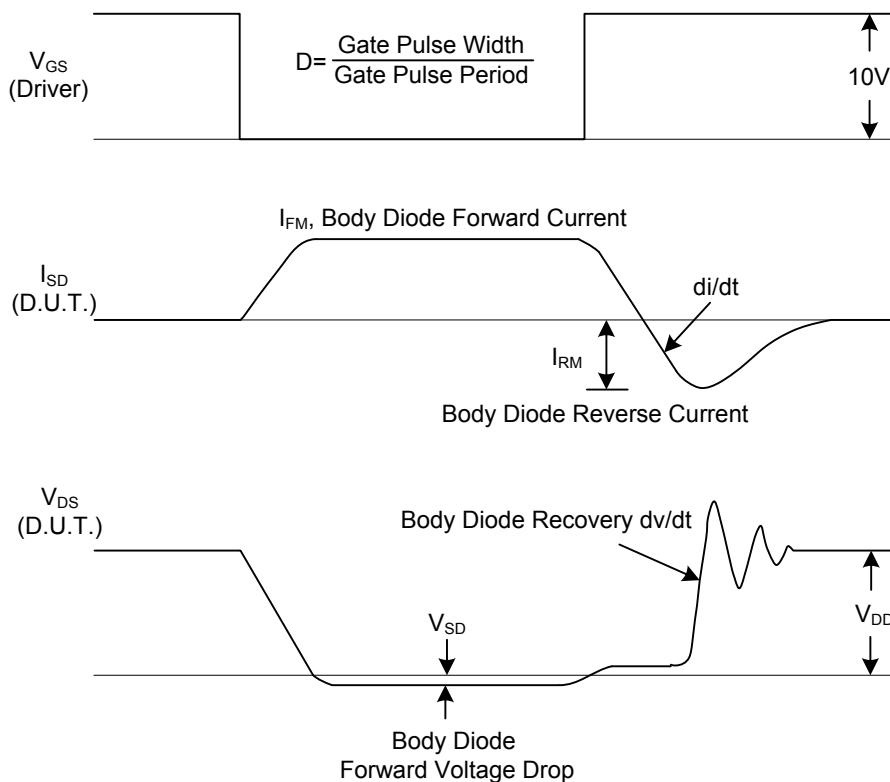


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)

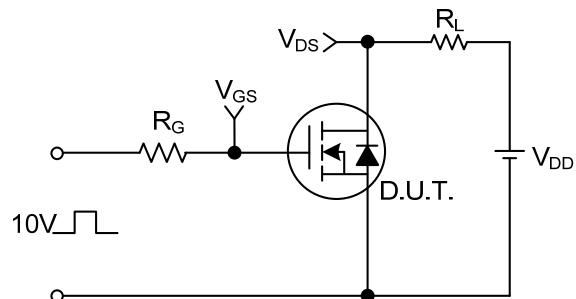


Fig. 2A Switching Test Circuit

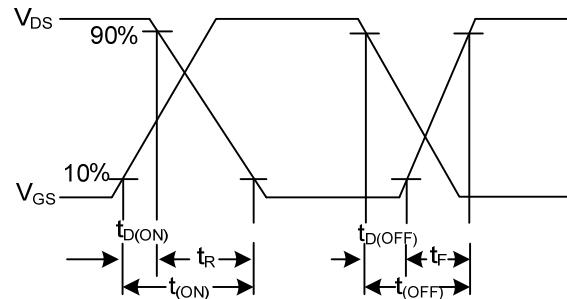


Fig. 2B Switching Waveforms

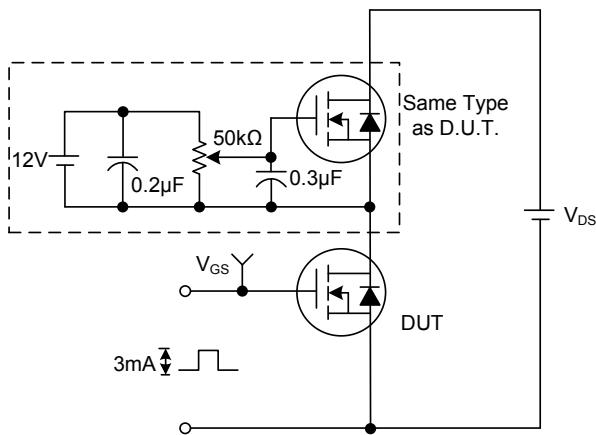


Fig. 3A Gate Charge Test Circuit

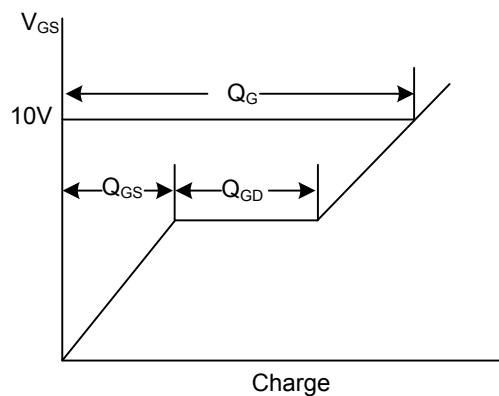


Fig. 3B Gate Charge Waveform

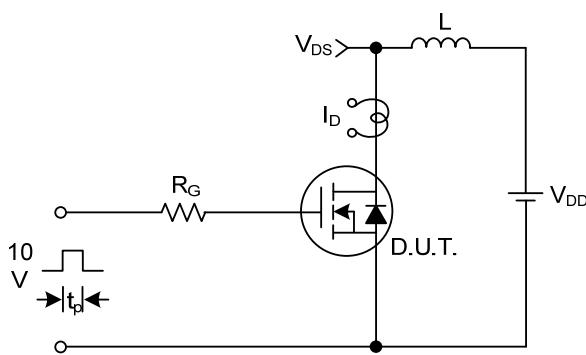


Fig. 4A Unclamped Inductive Switching Test Circuit

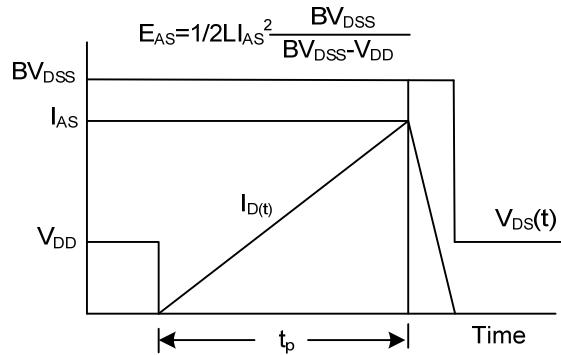
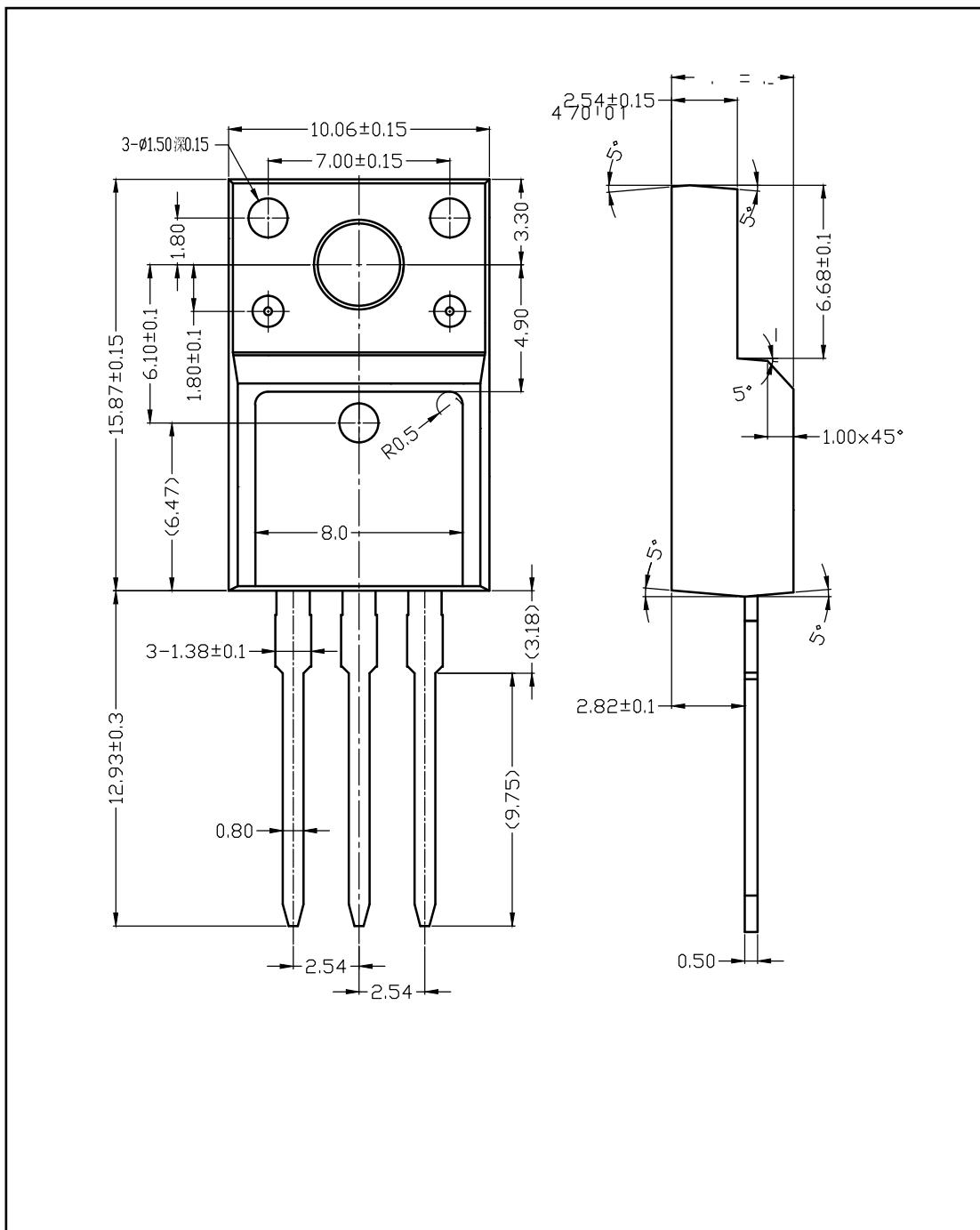


Fig. 4B Unclamped Inductive Switching Waveforms

■ TO-220F-3L PACKAGE OUTLINE DIMENSIONS



■ TO-220-3L PACKAGE OUTLINE DIMENSIONS

